

# MG048A150004A

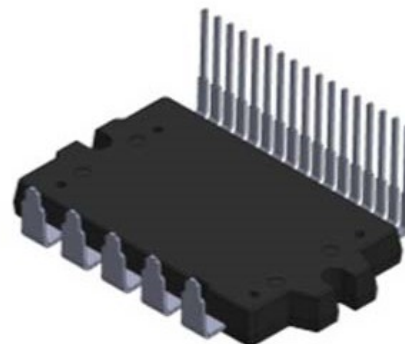
## 3 phase Inverter Module

### Feature

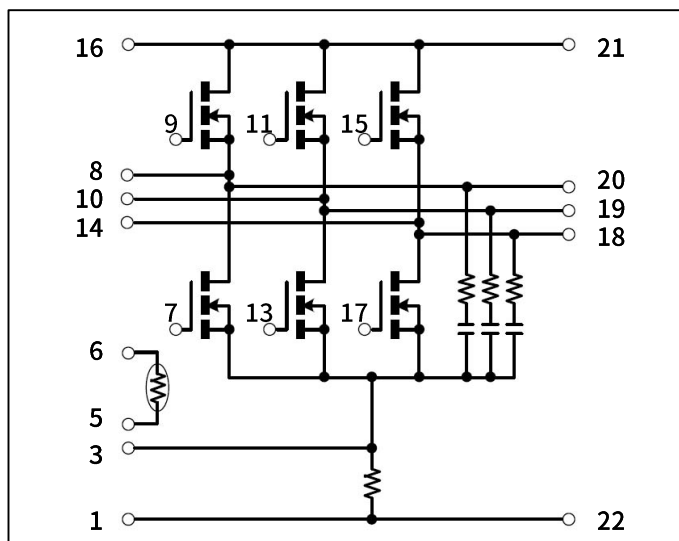
- 3 phase Inverter
- MOSFET(N-channel)
- High current capacity
- Isolated package
- Low Ron
- Halogen free
- Pb free terminal
- RoHS:Yes

### Outline

House Name: MG048



### Equivalent circuit



Absolute maximum ratings (Tc = 25°C unless otherwise specified)

MOSFET

Item	Symbol	Conditions	Ratings	Unit
Channel temperature	T <sub>ch</sub>		150	°C
Drain-source voltage	V <sub>DSS</sub>		40	V
Gate-source voltage	V <sub>GSS</sub>		±20	V
Continuous drain current (DC)	I <sub>D</sub>		150	A
Continuous drain current (Peak)	I <sub>DP</sub>	Pulse width 10μs, Duty = 1/100	600	A
Total power dissipation	P <sub>T</sub>		147	W
Single avalanche current	I <sub>AS</sub>	Starting T <sub>ch</sub> =25°C T <sub>ch</sub> ≤150°C	77	A
Single avalanche energy	E <sub>AS</sub>	Starting T <sub>ch</sub> =25°C T <sub>ch</sub> ≤150°C	730	mJ

Module

Item	Symbol	Conditions	Ratings	Unit
Storage temperature	T <sub>stg</sub>		-40~125	°C
Mounting torque	TOR	Fixing screw M3	1.2	N·m

Electrical and thermal characteristics (Tc=25°C unless otherwise specified.)

MOSFET

Item	Symbol	Conditions	Ratings			Unit	
			Min.	Typ.	Max.		
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	40	—	—	V	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V	—	—	1.0	μA	
Gate-source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	—	—	±0.1	μA	
Static drain-source on-state resistance	R <sub>DS(ON)</sub>	Chip	I <sub>D</sub> =75A, V <sub>GS</sub> =10V	—	1.02	—	mΩ
		Terminal	I <sub>D</sub> =75A, V <sub>GS</sub> =10V (Electrical characteristics of Q6)	—	2.1	2.7	mΩ
Gate threshold voltage	V <sub>TH</sub>	I <sub>D</sub> =1mA, V <sub>DS</sub> =10V	2.0	3.0	4.0	V	
Source-drain diode forward voltage	V <sub>SD</sub>	I <sub>S</sub> =150A, V <sub>GS</sub> =0V	—	—	1.5	V	
Total gate charge	Q <sub>g</sub>	V <sub>DD</sub> =32V, V <sub>GS</sub> =10V, I <sub>D</sub> =150A	—	111	—	nC	
Gate to source charge	Q <sub>gs</sub>		—	32	—		
Gate to drain charge	Q <sub>gd</sub>		—	57	—		
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz (Electrical characteristics of discrete MOSFET device)	—	5900	—	pF	
Reverse transfer capacitance	C <sub>rss</sub>		—	590	—		
Output capacitance	C <sub>oss</sub>		—	1100	—		

Turn—on delay time	td(on)	$I_D=87.5A, R_L=0.23\Omega,$ $V_{DD}=20V, R_g=0\Omega$ $V_{GS(+)}=10V, V_{GS(-)}=0V,$ (Electrical characteristics of discrete MOSFET device)	—	12	—	ns
Rise time	tr		—	117	—	
Turn—off delay time	td(off)		—	52	—	
Fall time	tf		—	32	—	
Diode reverse recovery time	trr	$I_F=150A,$ $V_{GS}=0V$	—	62	—	ns
Diode reverse recovery charge	Qrr	$di/dt=100A/\mu s$	—	39	—	nC

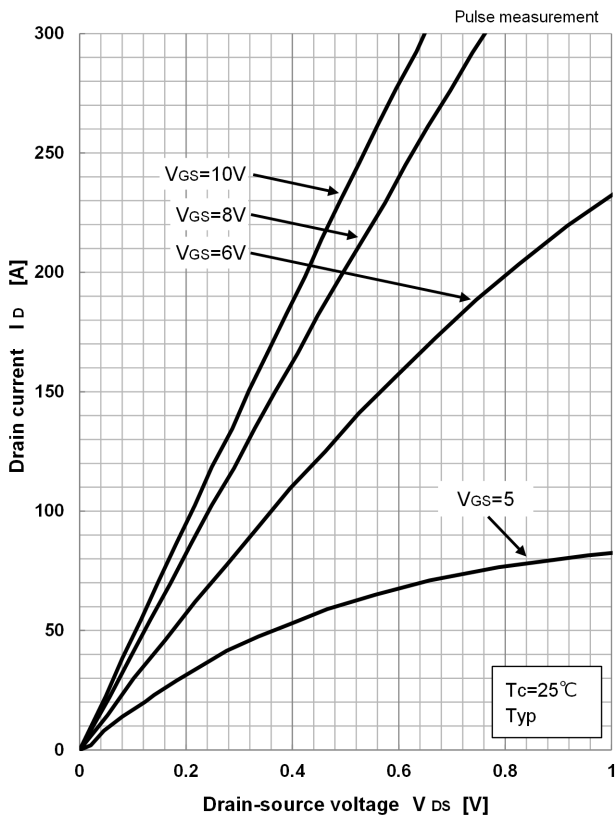
#### Module

Item	Symbol	Conditions	Ratings			Unit
			Min.	Typ.	Max.	
Thermal resistance	$R_{th(j-c)}$	Junction to case, with heatsink	—	—	0.85	°C/W

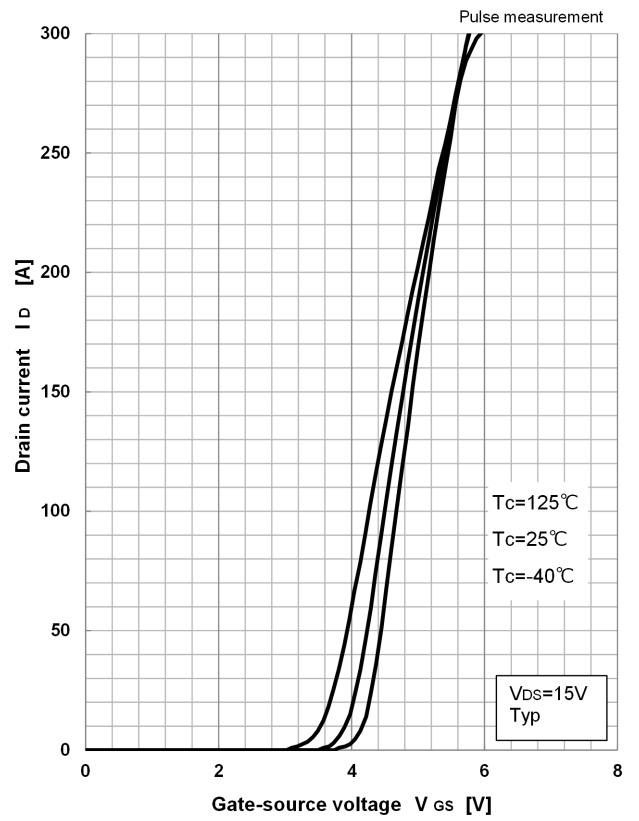
Note : Thermal resistance was measured at Q3

# CHARACTERISTIC DIAGRAMS

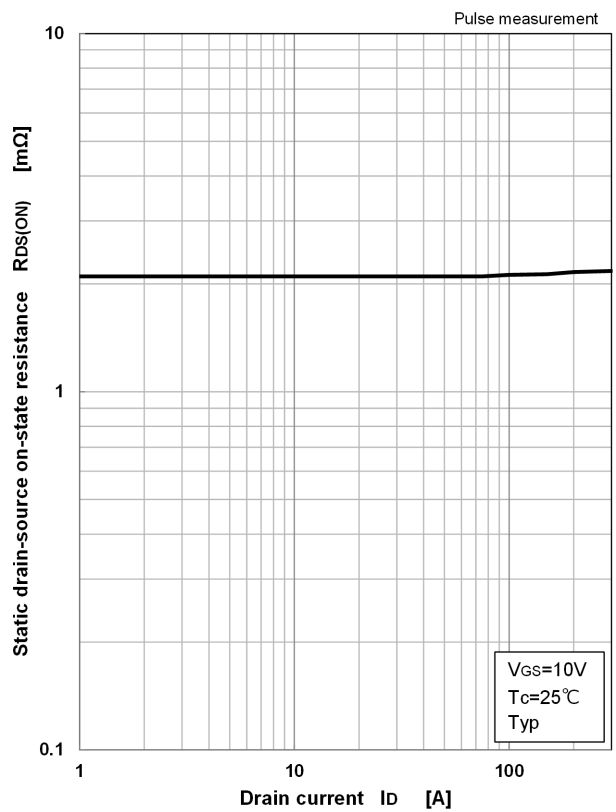
**Typical output characteristics**



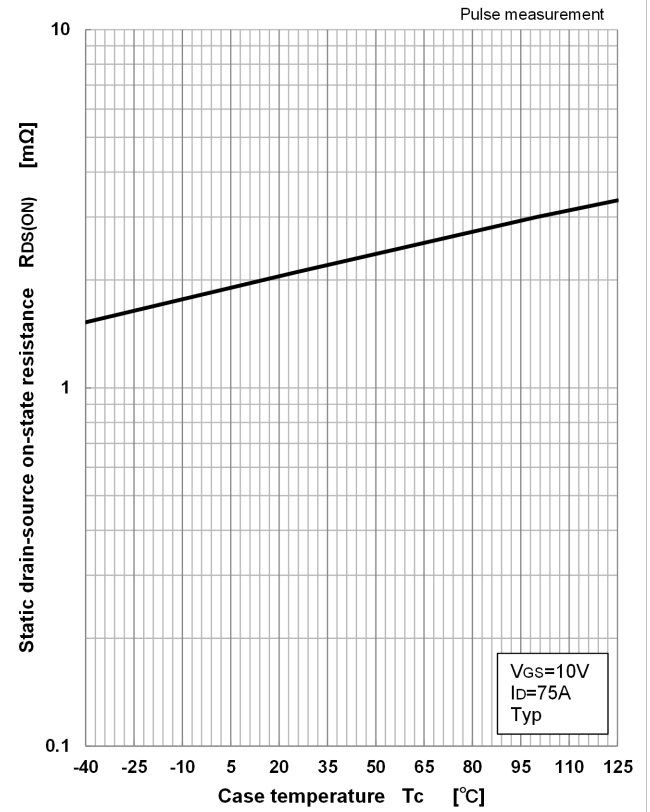
**Transfer characteristics**



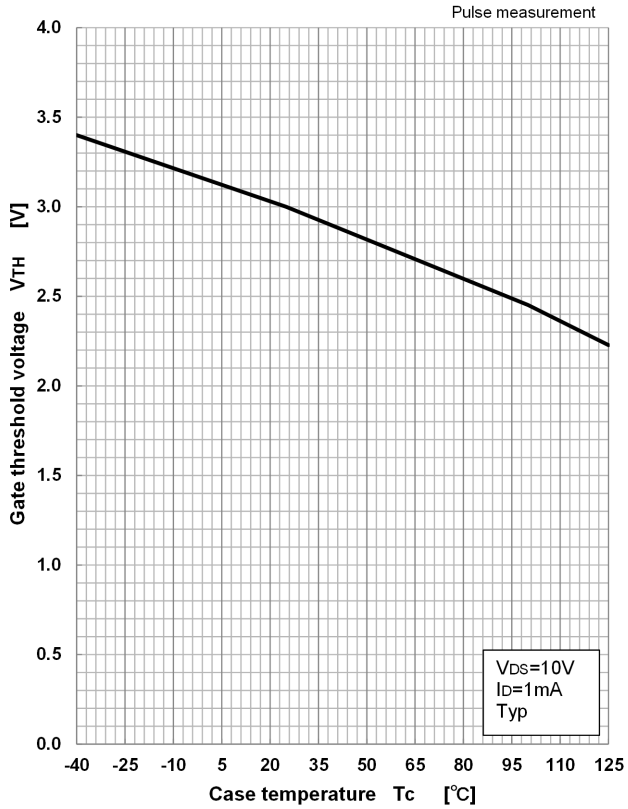
**Static drain-source on-state resistance vs drain current**



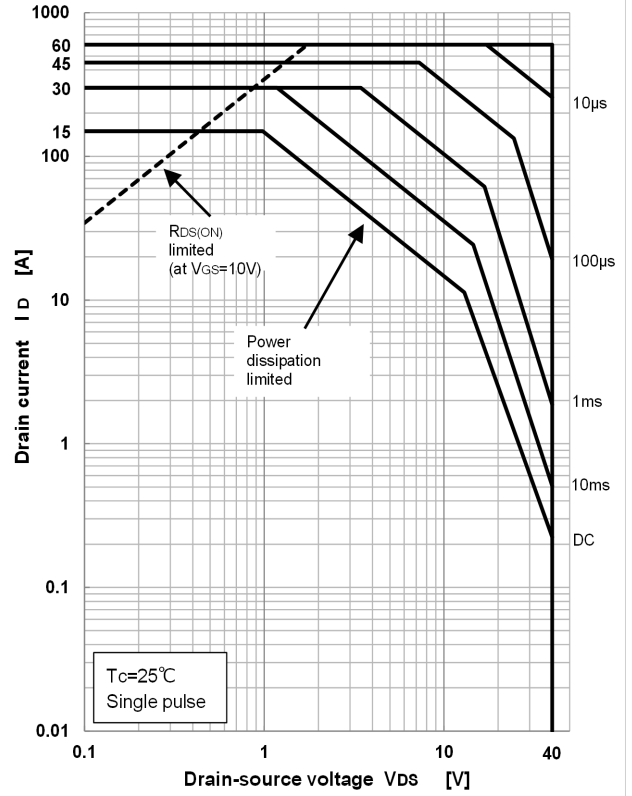
**Static drain-source on-state resistance vs case temperature**



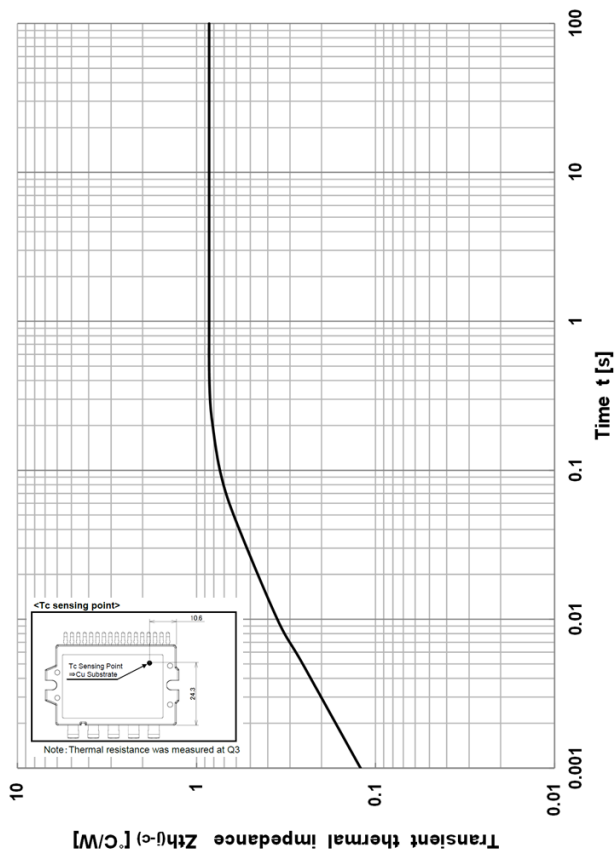
### Gate threshold voltage vs case temperature



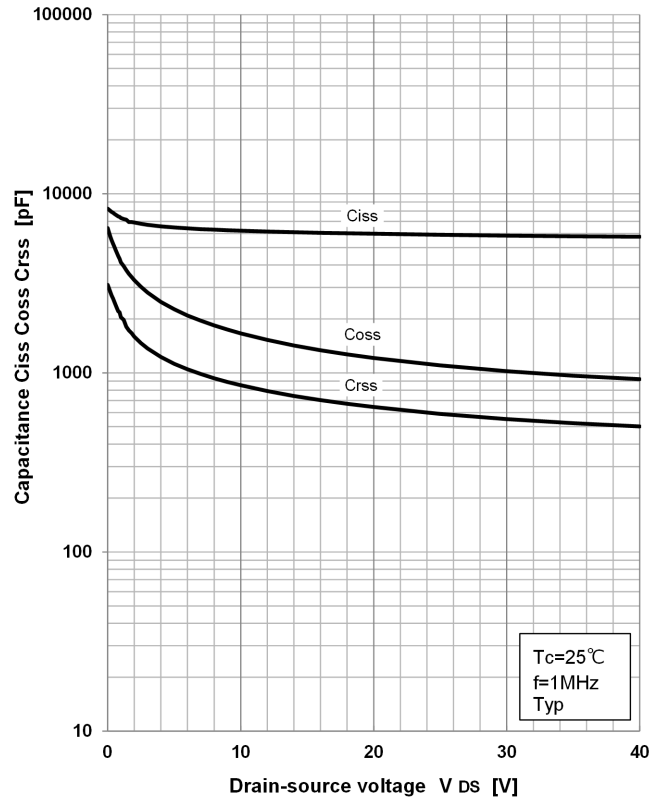
### Safe operating area



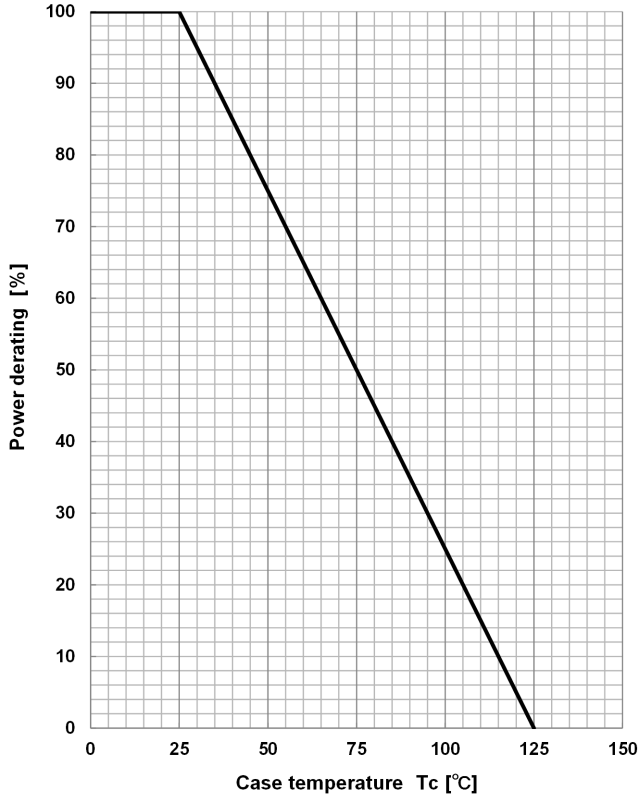
### Transient thermal impedance



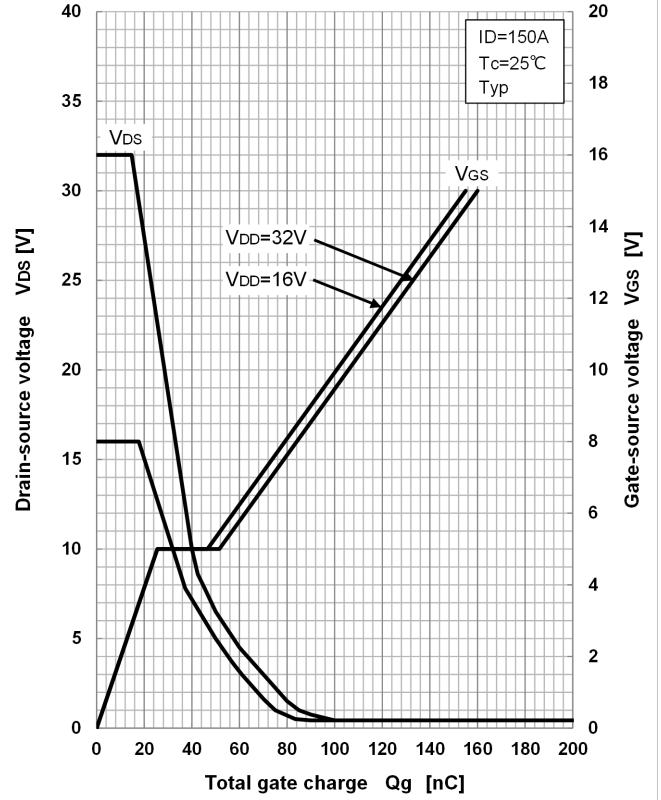
### Capacitance characteristics



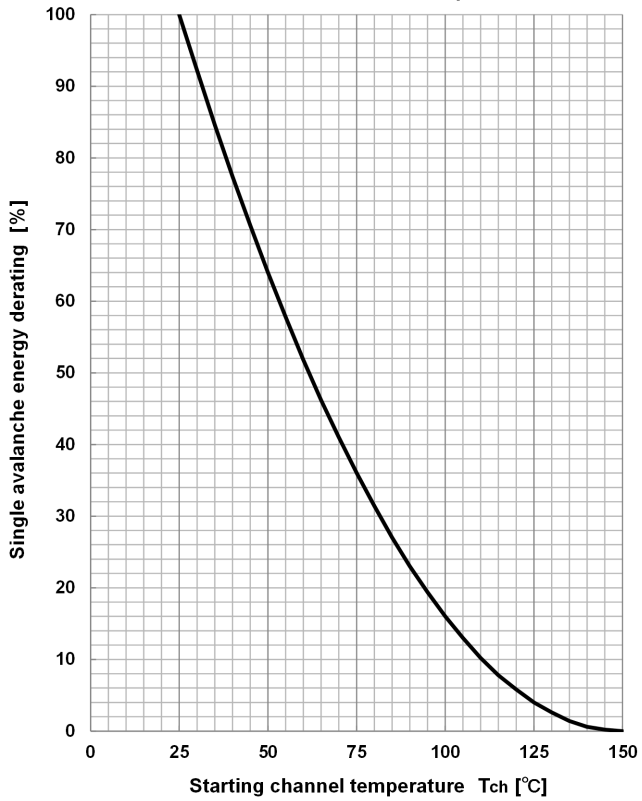
**Power derating vs case temperature**



**Gate charge characteristics**



**Single avalanche energy derating vs channel temperature**

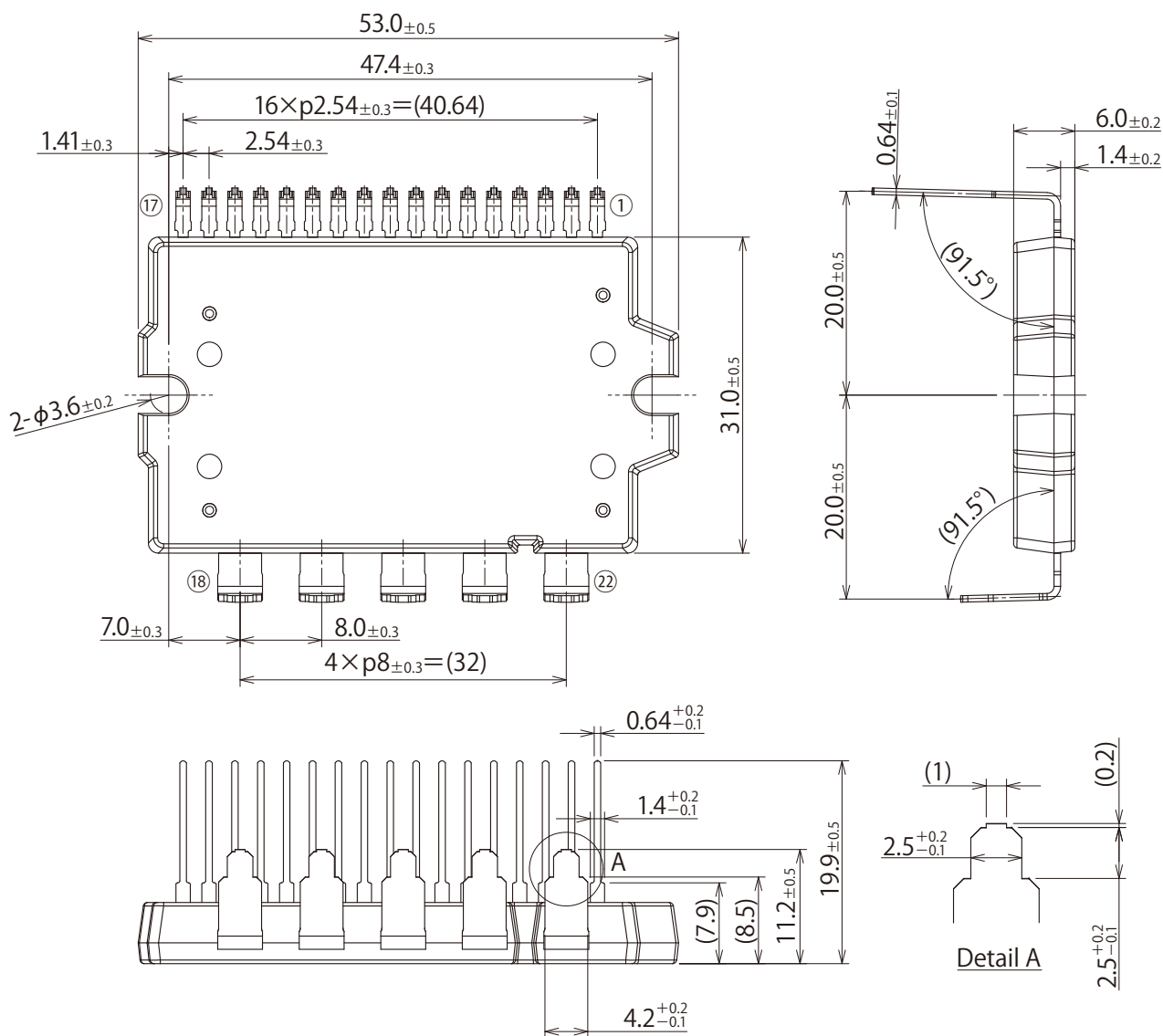


# Package Outline-Dimensions

unit : mm

F8

JEDEC Code	-
JEITA Code	-
House Name	MG048



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